PHYSICAL REVIEW B **80**, 049905(E) (2009)

Erratum: Formation of epitaxial gold nanoislands on (100) silicon [Phys. Rev. B 78, 035305 (2008)]

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(Received 1 July 2009; published 22 July 2009)

DOI: 10.1103/PhysRevB.80.049905 PACS number(s): 68.35.Fx, 61.05.C−, 61.46.−w, 68.37.Lp, 99.10.Cd

Figures 3 and 4 of this paper are identical. The correct Fig. 3 is below. Since the latter is what was intended, no other aspects of the paper are affected by this change. We thank Wissal Alayashi for pointing this out.

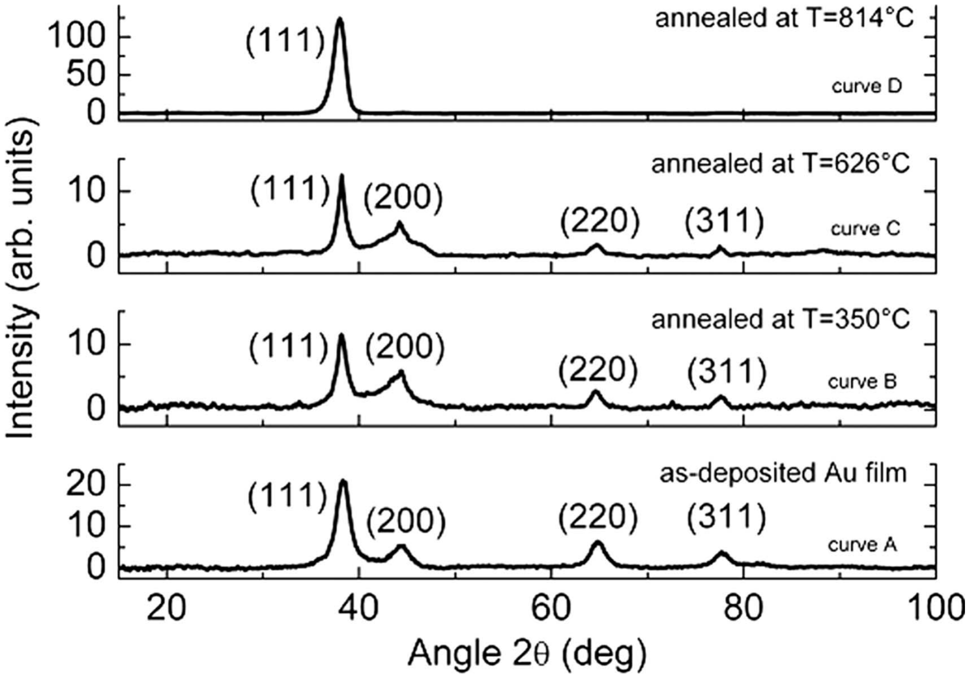

FIG. 3. GIXRD patterns on the as-deposited (curve A) and the Au-films annealed at T=350 °C (curve B), 626 °C (curve C) and 814 °C (curve D), respectively. The 2θ scans were recorded at fixed incidence angle $\omega_i = 1.0°$ and by using CuKα-radiation. The patterns show the typical Au peaks for the as-deposited and annealed (T < 626 °C) samples, while the Au-film annealed at 814 °C exhibits a single very intense (111) Au peak indicating a pronounced texture.